

Amendments to the Claims:

This listing of claims replaces any and all prior claim lists.

Listing of Claims:

Claim 1 (original). A method for manufacturing a compound semiconductor epitaxial substrate comprising a step of epitaxially growing an InGaAs layer on an InP single crystal substrate or on an epitaxial layer lattice-matched to the InP single crystal substrate under conditions of

ratio of V/III: 10 - 100,

growth temperature: 630°C - 700°C, and

growth rate: 0.6 µm/h - 2 µm/h.

Claim 2 (original). The method according to claim 1, wherein the InP single crystal substrate has a plane direction accuracy of $\pm 0.05^\circ$ in the (100).

Claim 3 (currently amended). The method according to claim 1 or 2 claim 1, wherein the epitaxially growing is carried out by using MOCVD metal-organic chemical vapor deposition (MOCVD).

Claim 4 (currently amended). The method according to any of claims 1-3 claim 1, wherein gallium raw material used for the epitaxially growing of the InGaAs layer includes use of gallium raw material is selected from the group consisting of trimethyl gallium and triethyl gallium.

Claim 5 (currently amended). The method according to ~~any of claims 1-4~~ claim 1, wherein ~~indium raw material used for the epitaxial growing of the InGaAs layer includes use of indium raw material comprising~~ trimethyl indium.

Claim 6 (currently amended). The method according to ~~any of claims 1-5~~ claim 1, wherein the epitaxial growing of the InGaAs layer includes use of arsenic raw material comprising arsine.

Claim 7 (original). A method for reducing concave defects in a compound semiconductor epitaxial substrate comprising a step of epitaxially growing an InGaAs layer on an InP single crystal substrate or on an epitaxial layer lattice-matched to the InP single-crystal substrate under conditions of

ratio of V/III: 10 to 100,

growth temperature: 630°C - 700°C, and

growth rate: 0.6 μm/h - 2 μm/h.

Claim 8 (currently amended). A compound semiconductor epitaxial substrate obtained by using the method according to ~~any of claims 1-6~~ claim 1.